Device Modeling Report

COMPONENTS: Power MOSFET (Standard)
PART NUMBER: 2SK2740
MANUFACTURER: ROHM
REMARK: Body Diode (Standard)

Bee Technologies Inc.

POWER MOSFET MODEL

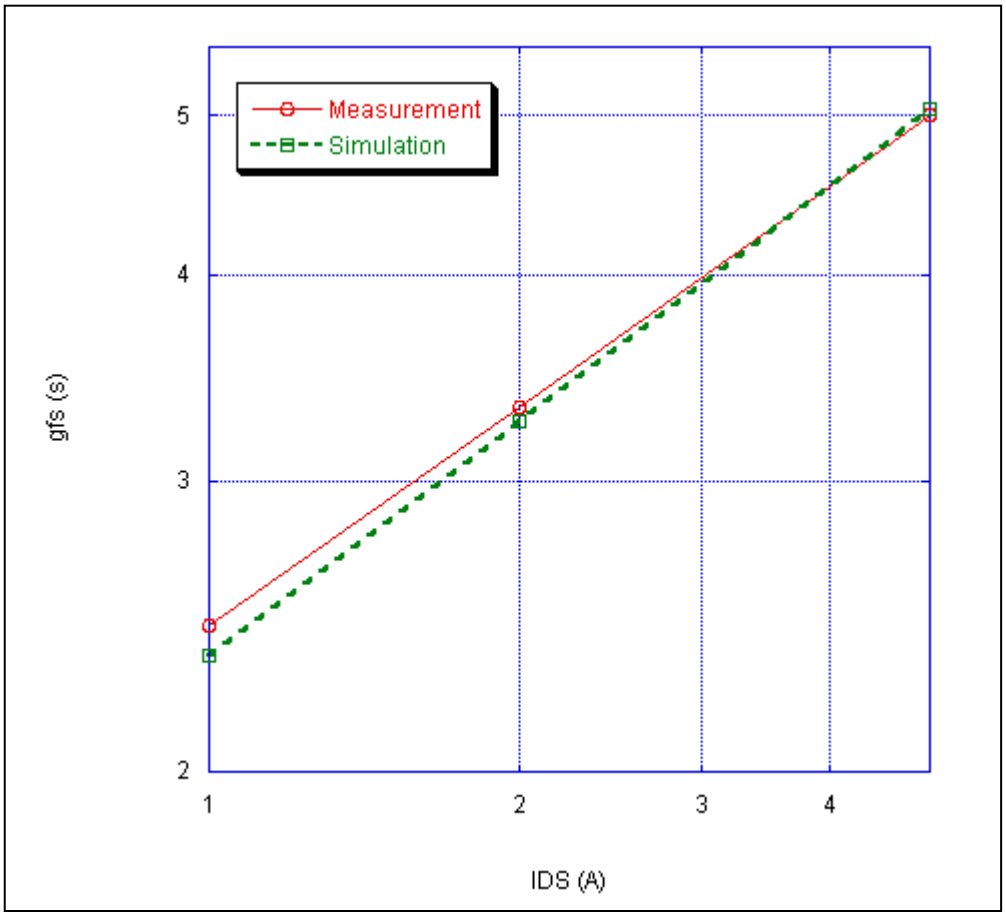
Pspice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Modility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Body Diode Model

Pspice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

Transconductance Characteristic

Circuit Simulation Result

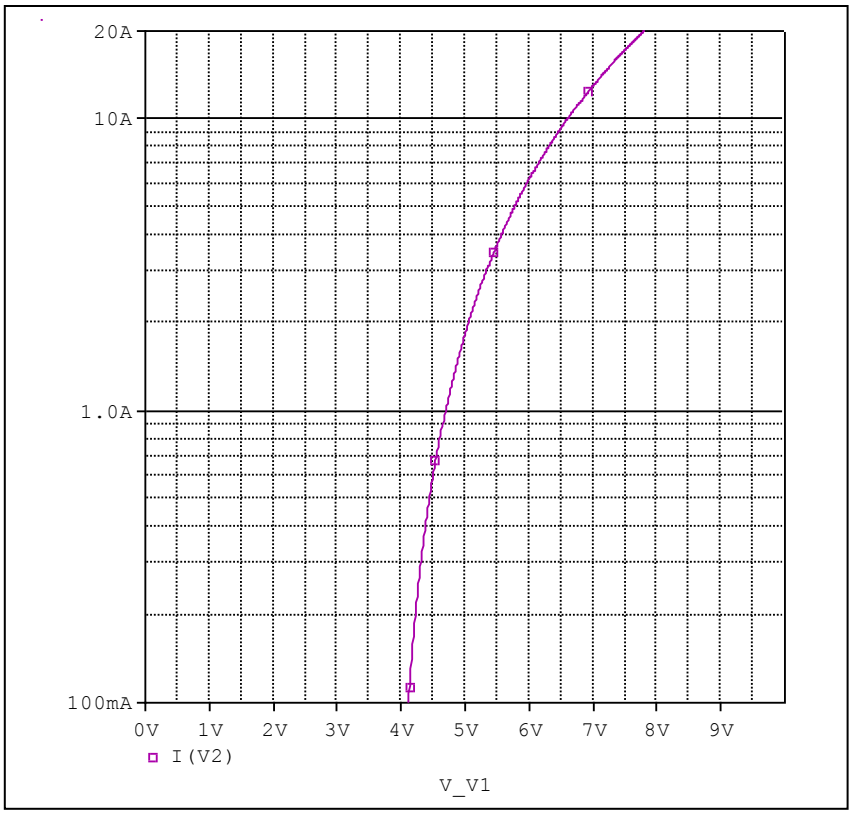


Comparison table

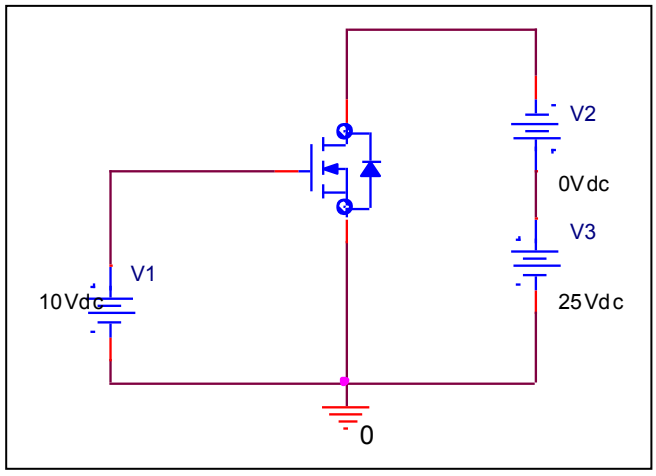
I_D(A)	V_{GS}(V)		Error (%)
	Measurement	Simulation	
1.000	2.450	2.350	-4.082
2.000	3.330	3.260	-2.102
5.000	5.000	5.050	1.000

Vgs-Id Characteristic

Circuit Simulation result

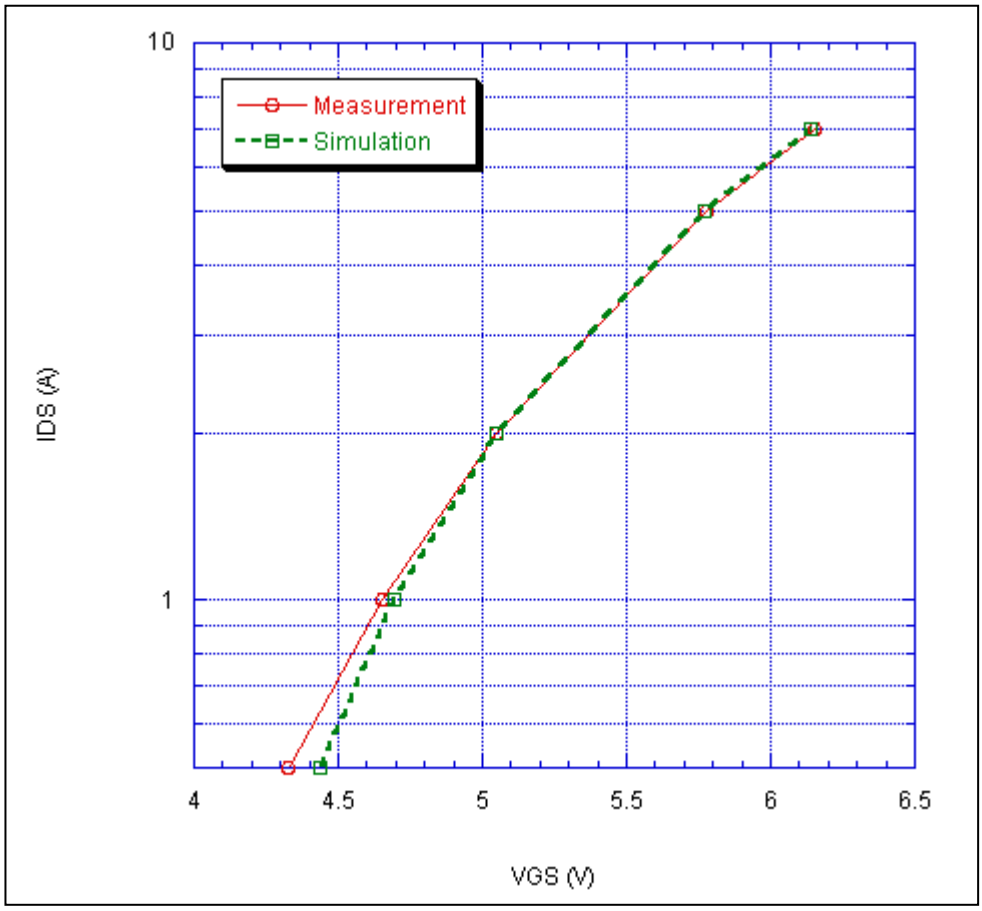


Evaluation circuit



Comparison Graph

Circuit Simulation Result

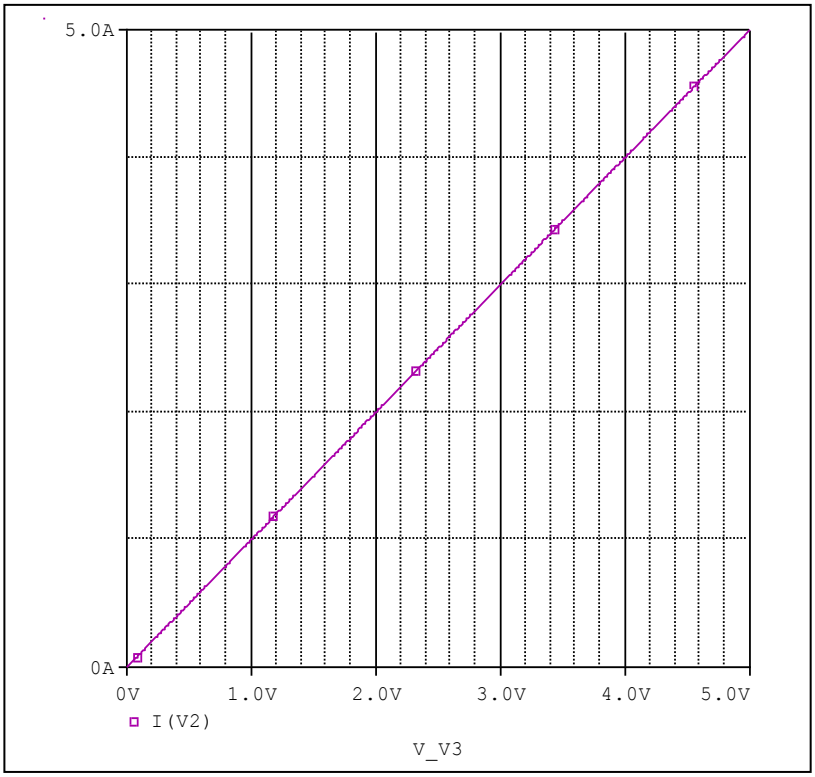


Simulation Result

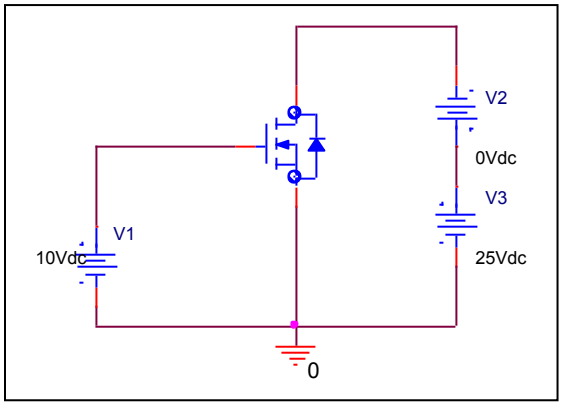
I_D(A)	V_{GS}(V)		Error (%)
	Measurement	Simulation	
0.500	4.330	4.440	2.540
1.000	4.650	4.694	0.946
2.000	5.050	5.052	0.040
5.000	5.780	5.772	-0.138
7.000	6.150	6.136	-0.228

Id-Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

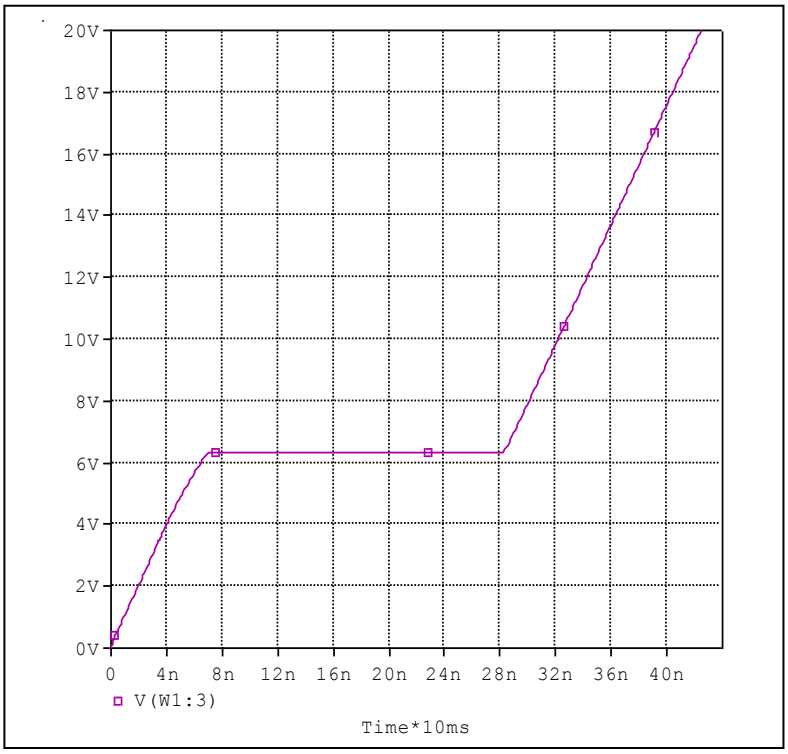


Simulation Result

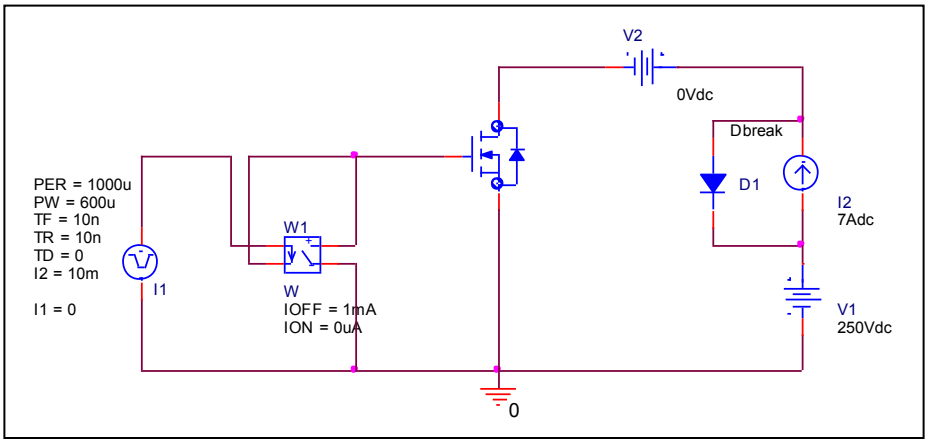
I_D=4, V_{GS}=10V	Measurement		Simulation		Error (%)
R_{DS} (on)	1.000	Ω	1.000	Ω	0.000

Gate Charge Characteristic

Circuit Simulation result



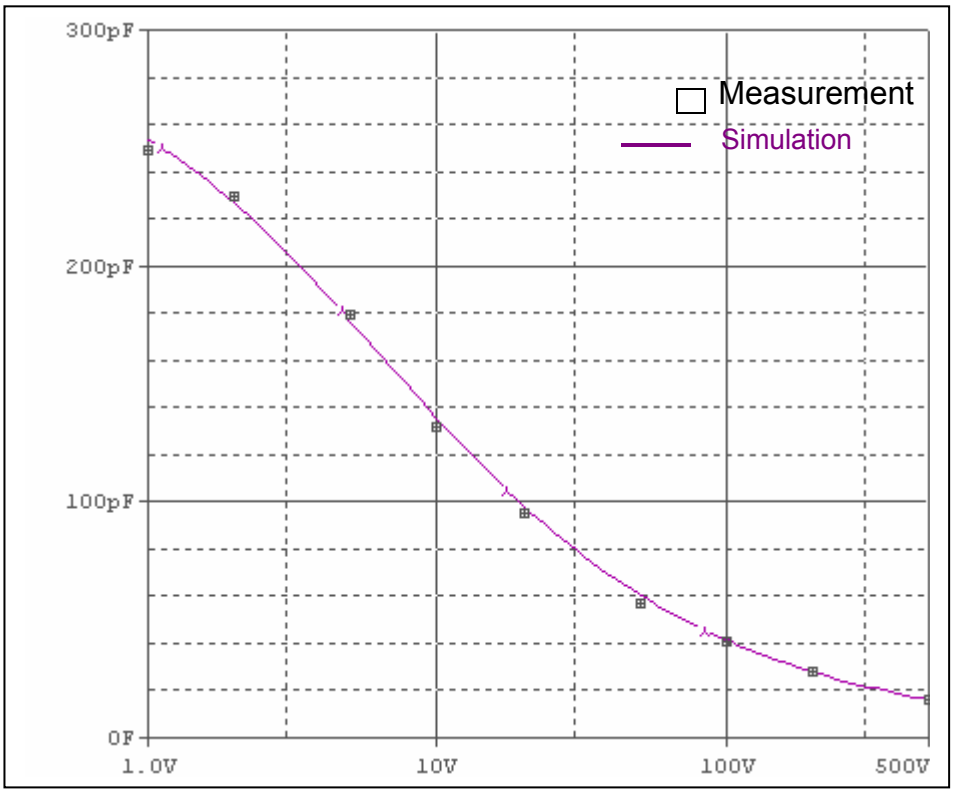
Evaluation circuit



Simulation Result

V_{DD}=250V ,I_D=7A	Measurement		Simulation		Error (%)
Qgs	7.200	nC	7.210	nC	0.139
Qgd	20.800	nC	20.790	nC	-0.048

Capacitance Characteristic (Vds vs. Cbd)

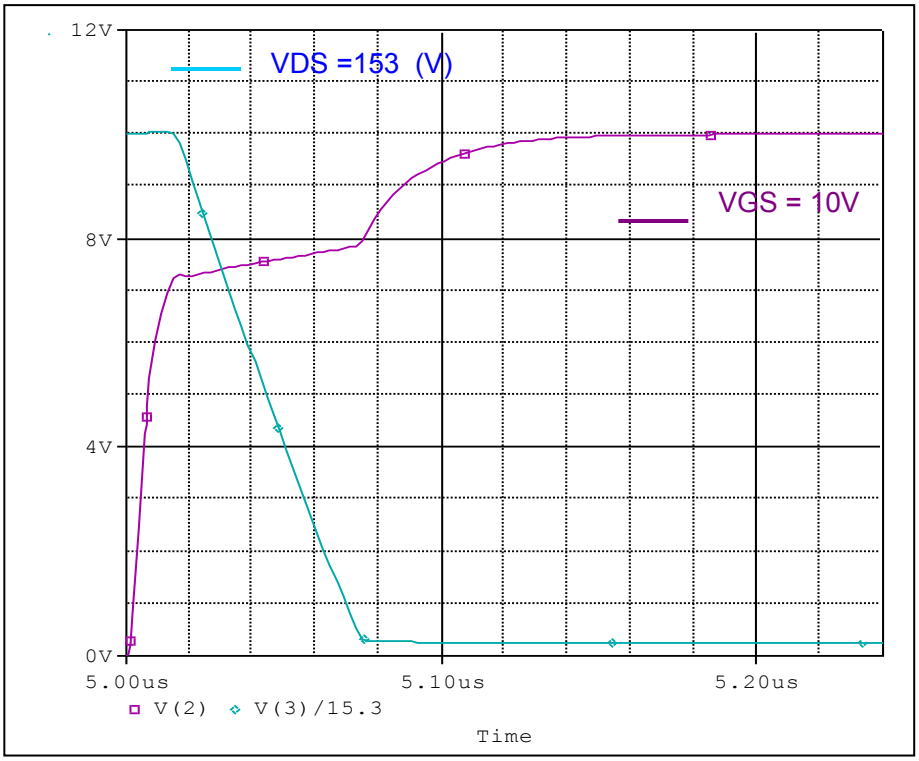


Simulation Result

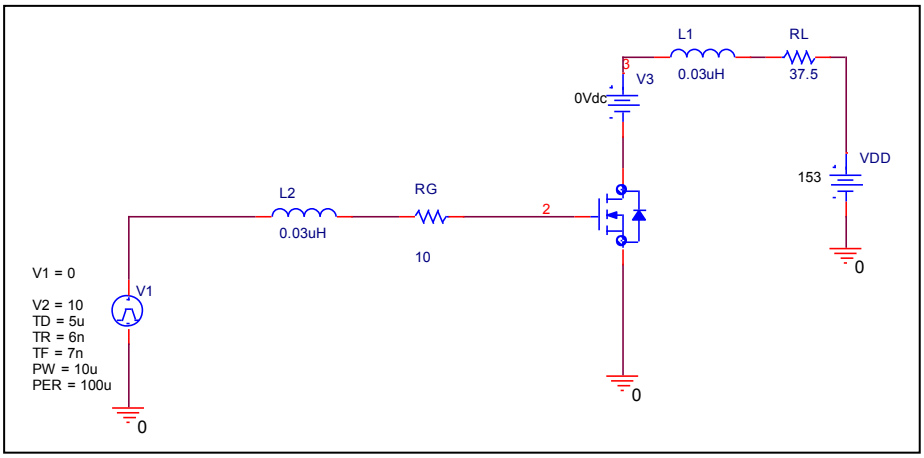
V_{DS}(V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
1.000	250.000	253.000	1.200
2.000	230.000	226.300	-1.609
5.000	180.000	176.500	-1.944
10.000	133.000	135.000	1.504
20.000	96.000	98.000	2.083
50.000	58.000	60.300	3.966
100.000	42.000	41.000	-2.381
200.000	29.000	28.000	-3.448
500.000	17.000	16.500	-2.941

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

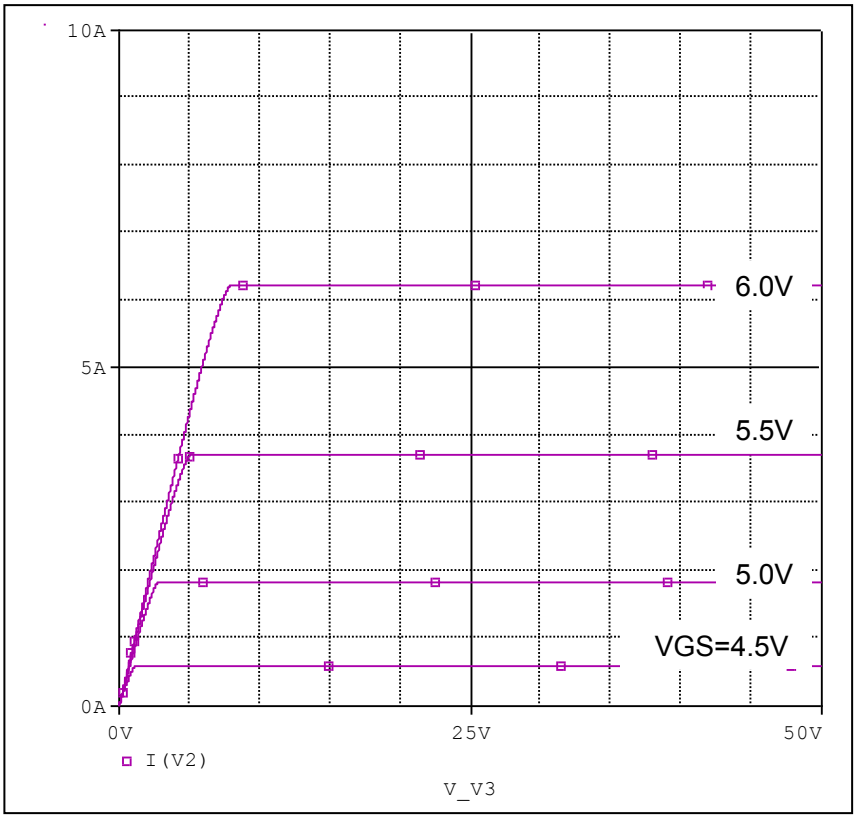


Simulation Result

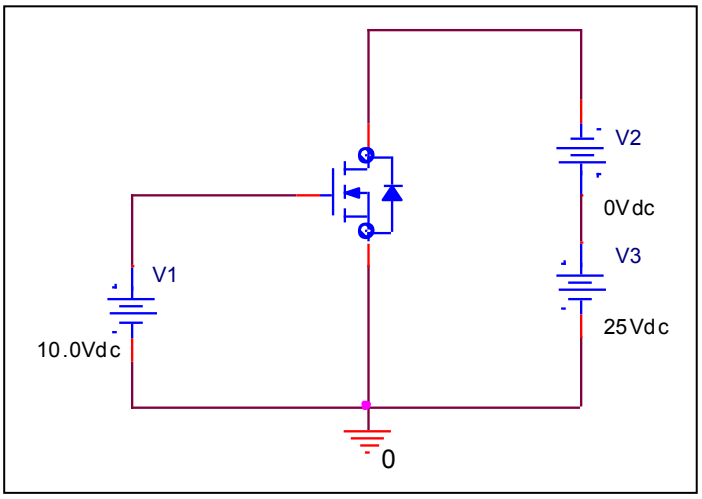
I_D=4A, V_{DD}=153V V_{GS}=0/10V	Measurement		Simulation		Error(%)
td (on)	19.000	ns	18.994	ns	-0.032

Output Characteristic

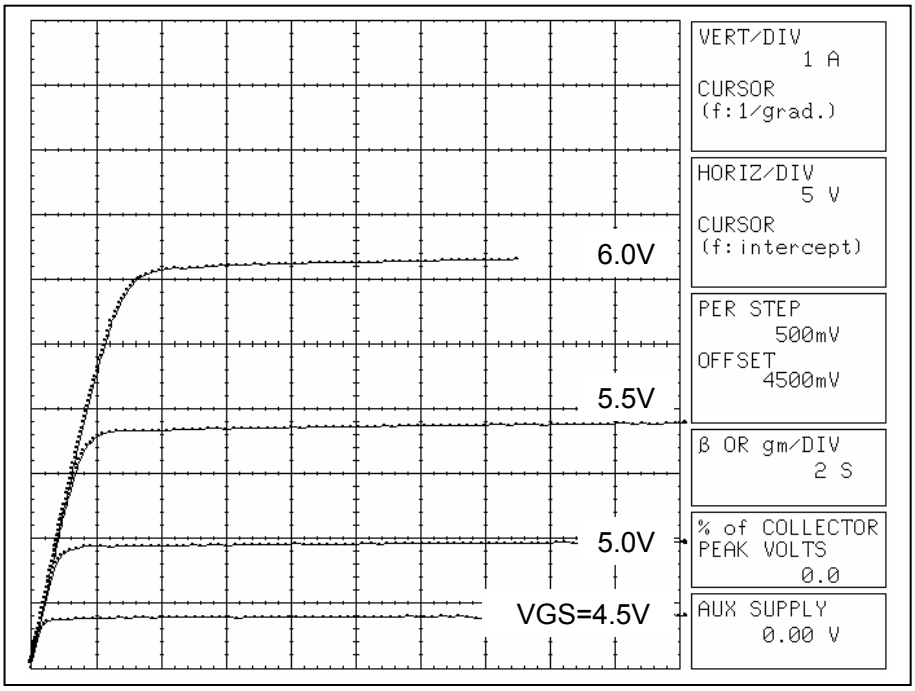
Circuit Simulation result



Evaluation circuit

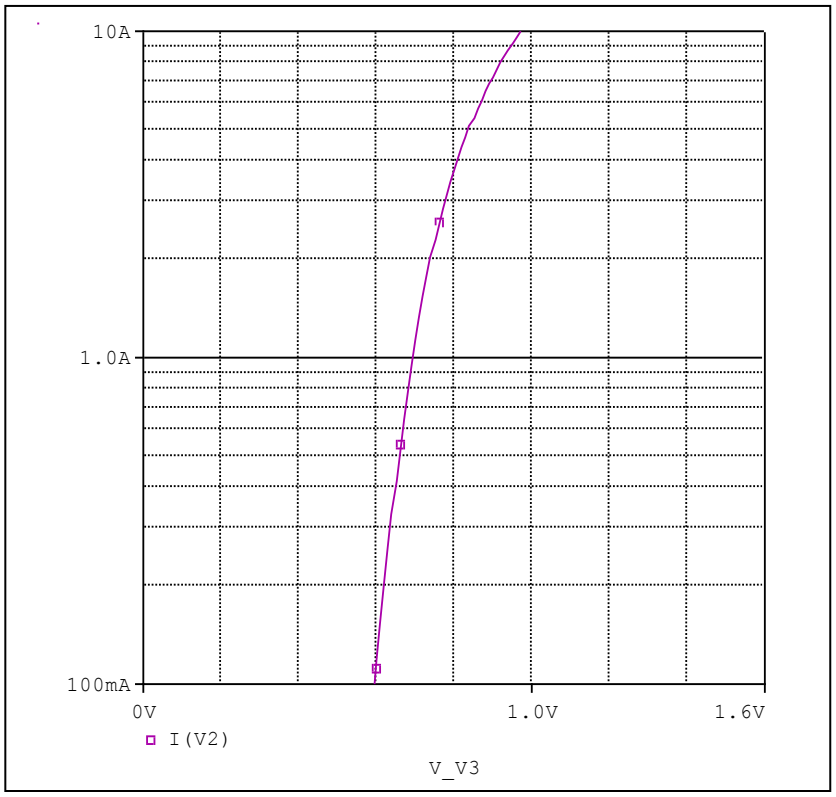


Output Characteristic Reference

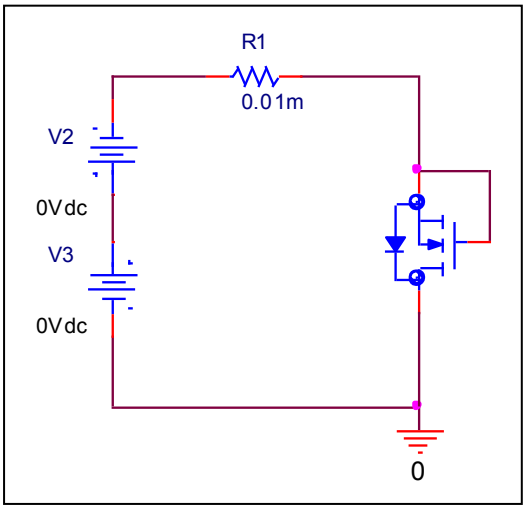


Forward Current Characteristic of Reverse Diode

Circuit Simulation Result

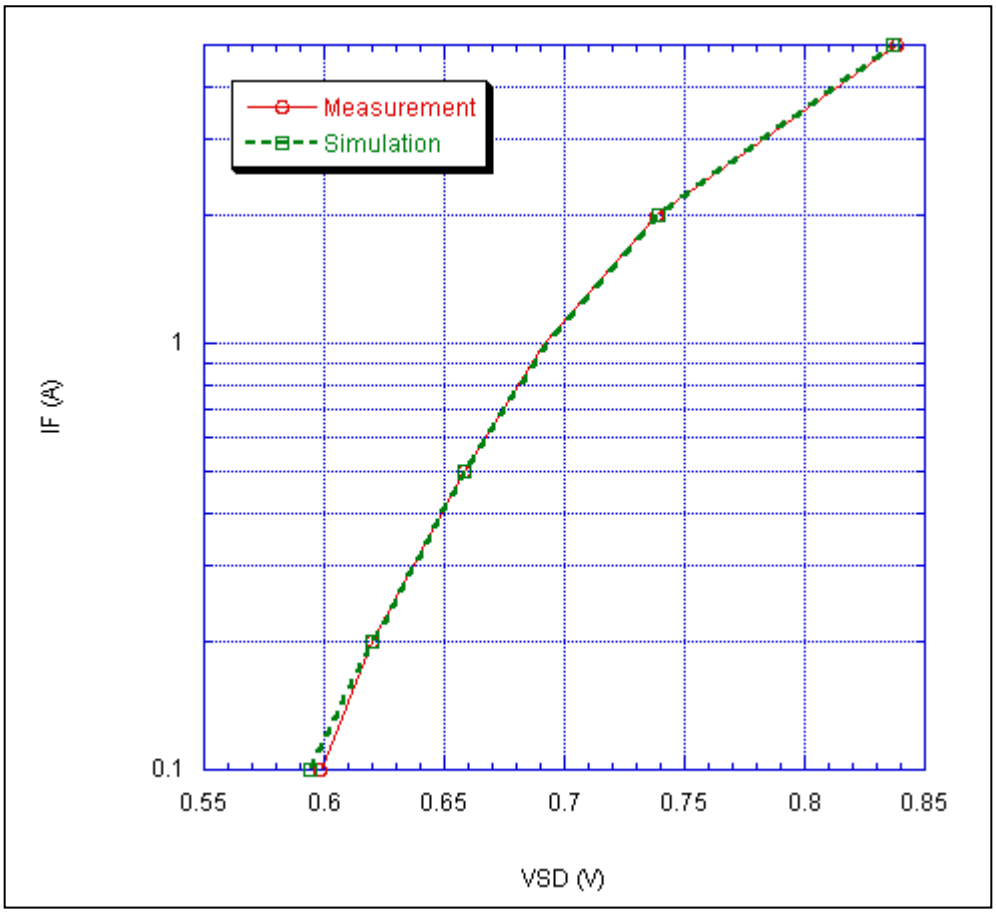


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

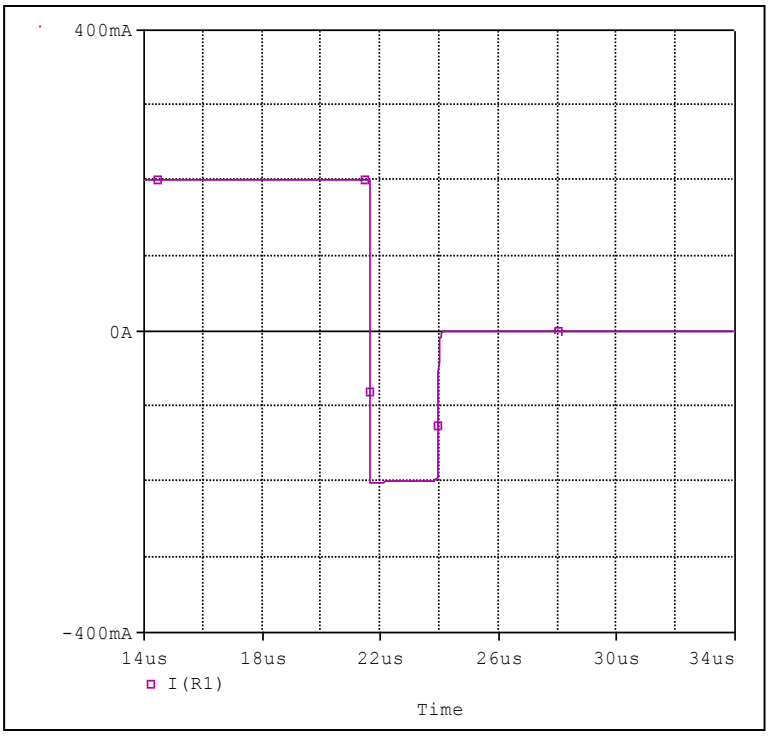


Simulation Result

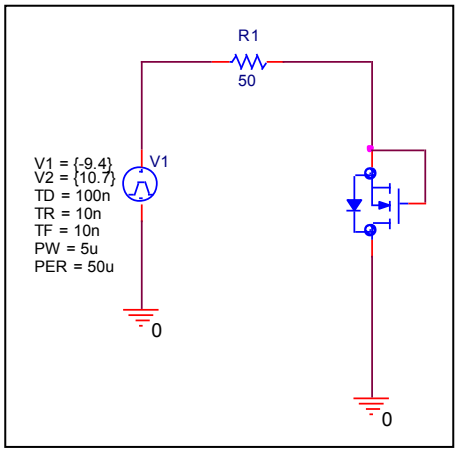
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.100	0.598	0.594	-0.669
0.200	0.620	0.620	-0.020
0.500	0.658	0.658	0.024
1.000	0.692	0.693	0.166
2.000	0.738	0.739	0.163
5.000	0.838	0.837	-0.097

Reverse Recovery Characteristic

Circuit Simulation Result



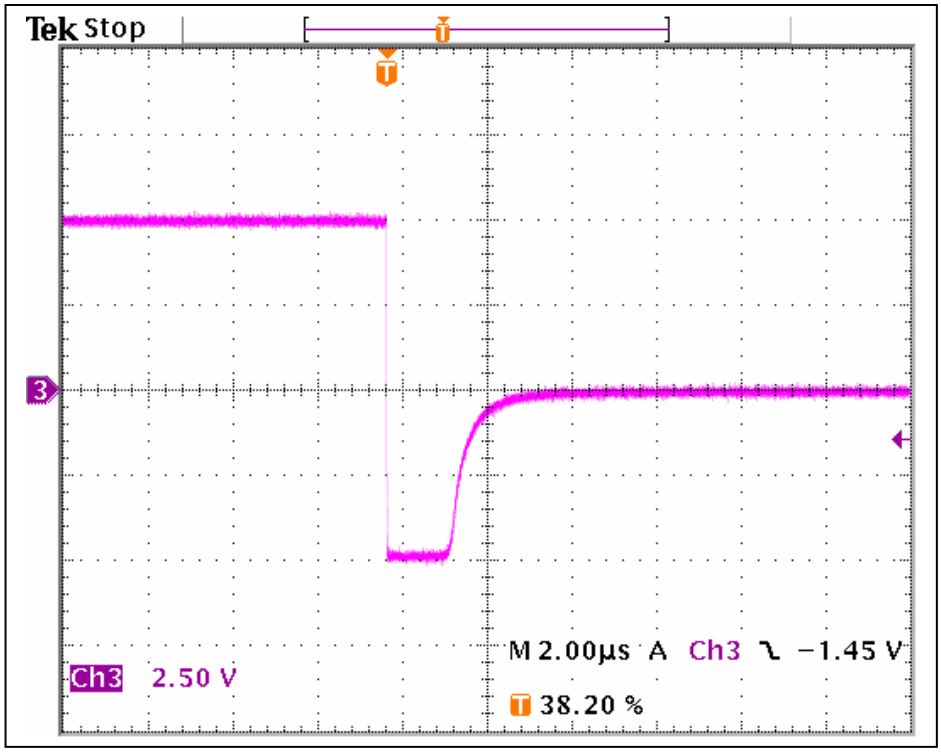
Evaluation Circuit



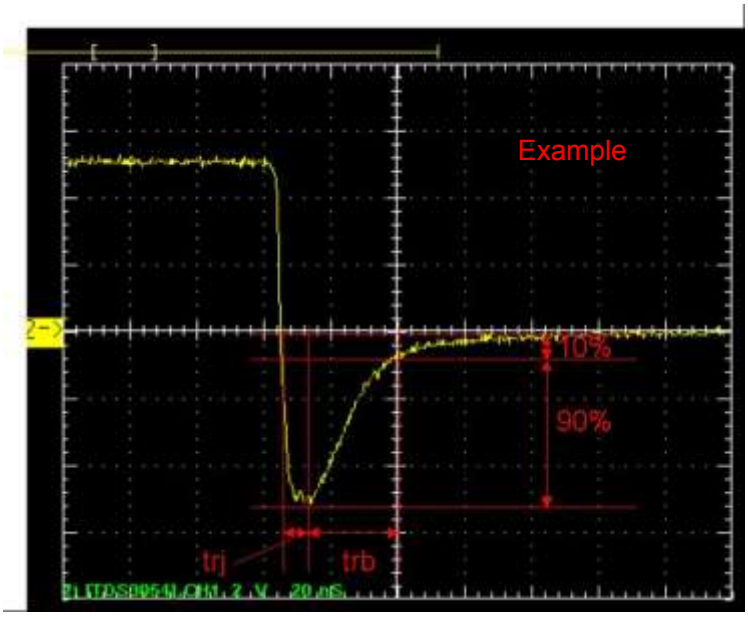
Compare Measurement vs. Simulation

	Measurement		Simulation		Error (%)
trr=trj+trb	**2.360**	**us**	**2.361**	**us**	**0.042**

Reverse Recovery Characteristic Reference



Trj=1.480(us)
Trb=0.880(us)
Conditions:Ifwd=Irev=0.2(A),Rl=50



Relation between trj and trb